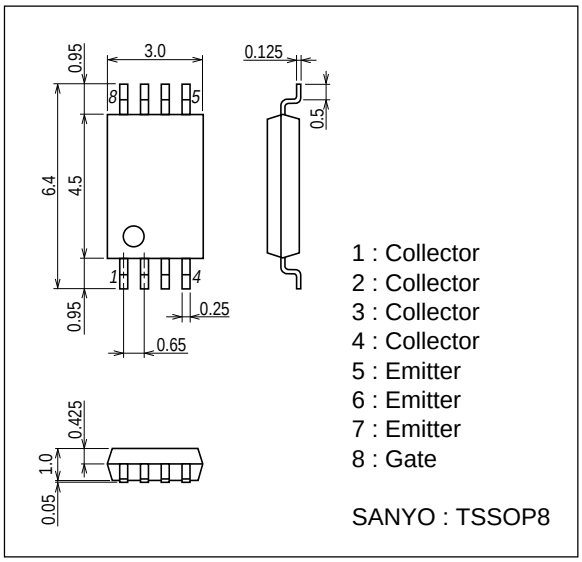
Continued from preceding page.

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Gate-to-Emitter Threshold Voltage	V_{GE}(off)	V_{CE}=10V, I_C=1mA	0.4		1.0	V
Collector-to-Emitter Saturation Voltage	V_{CE}(sat)	I_C=150A, V_{GE}=2.5V		3.7	5.5	V
Input Capacitance	Cies	V_{CE}=10V, f=1MHz		3800		pF
Output Capacitance	Coes	V_{CE}=10V, f=1MHz		58		pF
Reverse Transfer Capacitance	Cres	V_{CE}=10V, f=1MHz		47		pF

Package Dimensions

unit : mm (typ)
7006A-007



Electrical Connection

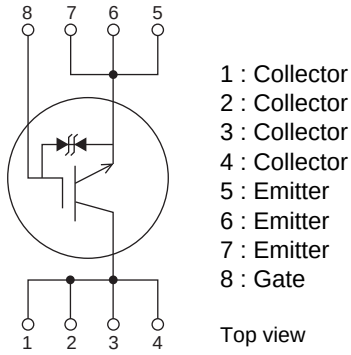
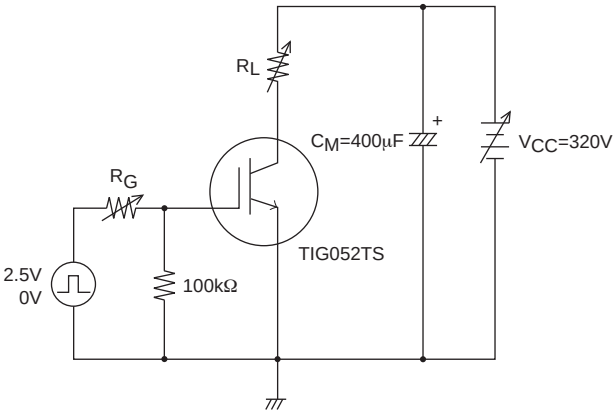
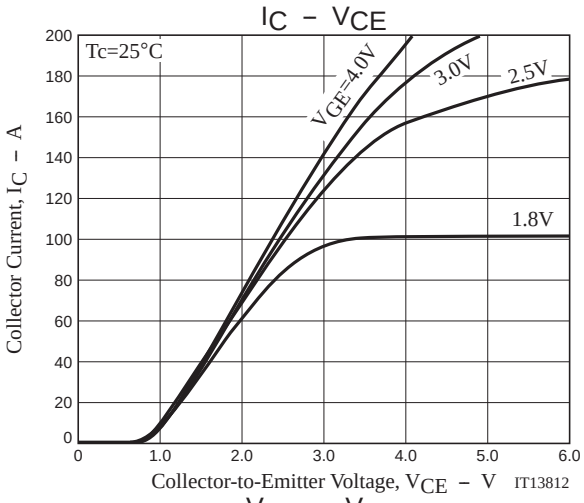
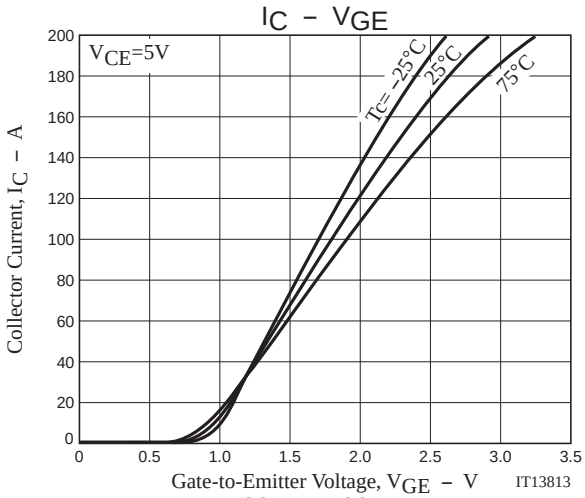


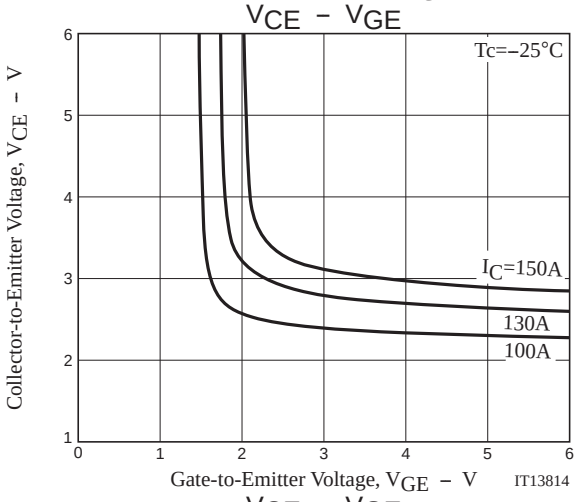
Fig.1 Large Current R Load Switching Circuit

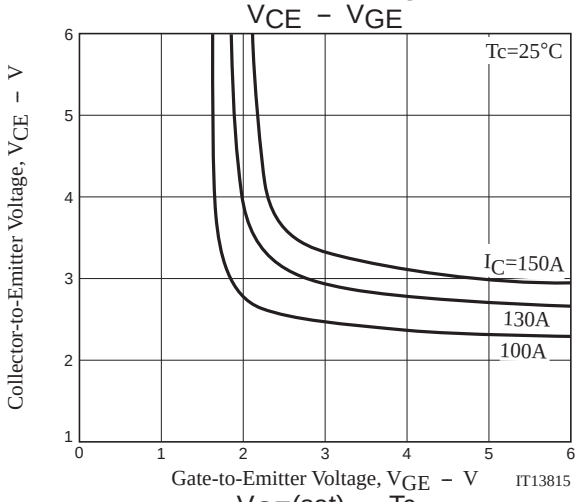


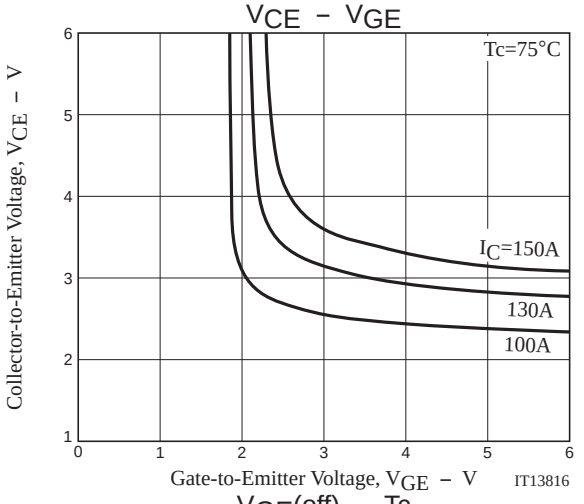
Note1. Gate Series Resistance $R_G \geq 82\Omega$ is recommended for prolection purpose at the time of turn OFF. However, if dv / dt≤400V / μs is satisfied at customer's actual set evaluation, $R_G < 82\Omega$ can also be used.
Note2. The collector voltage gradient dv / dt must be smaller than 400V / μs to protect the device when it is turned off.

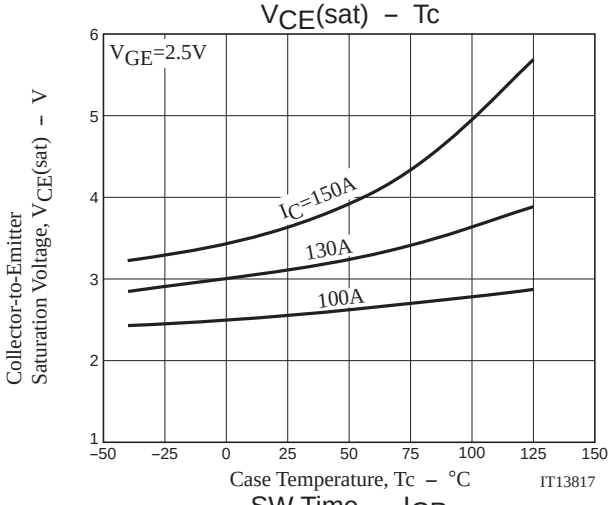


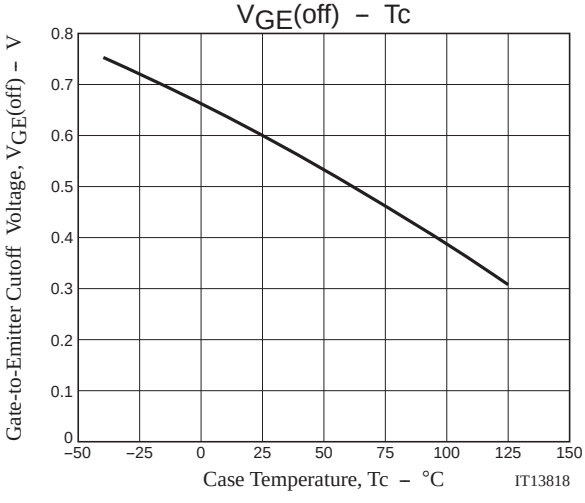


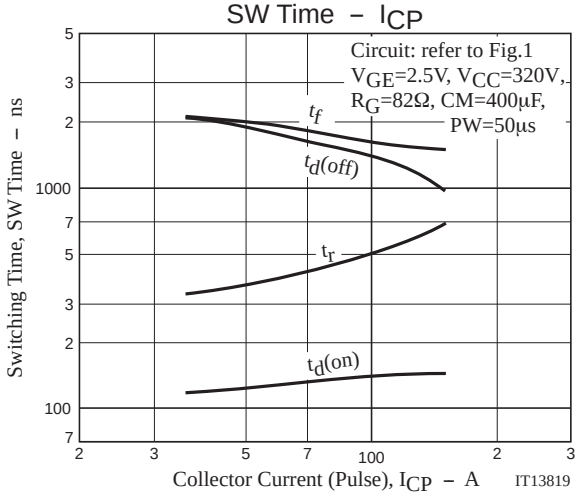




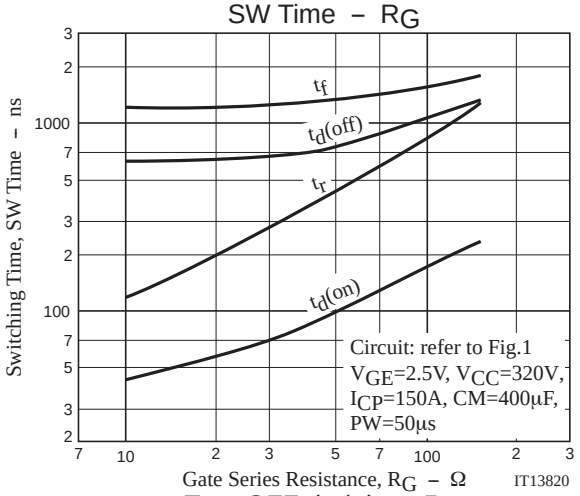




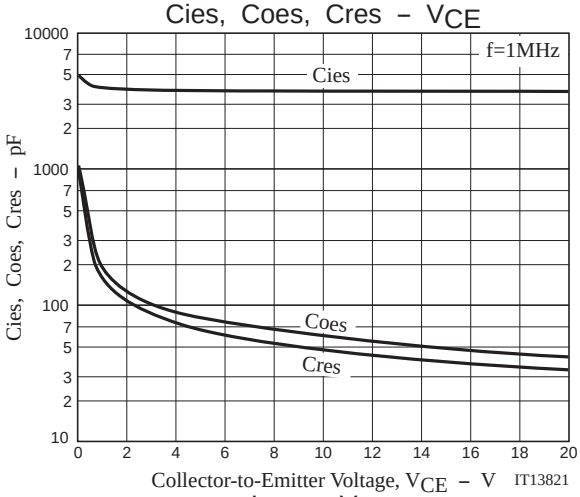




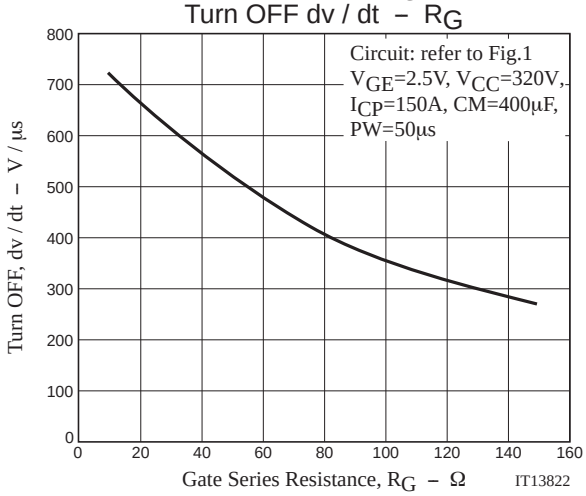
SW Time – R_G



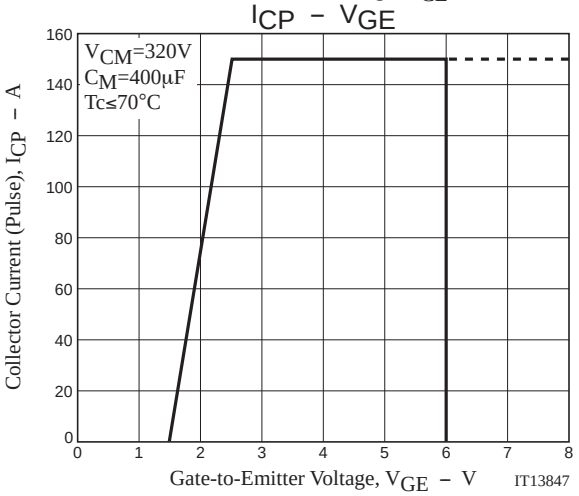
Cies, Coes, Cres – V_{CE}



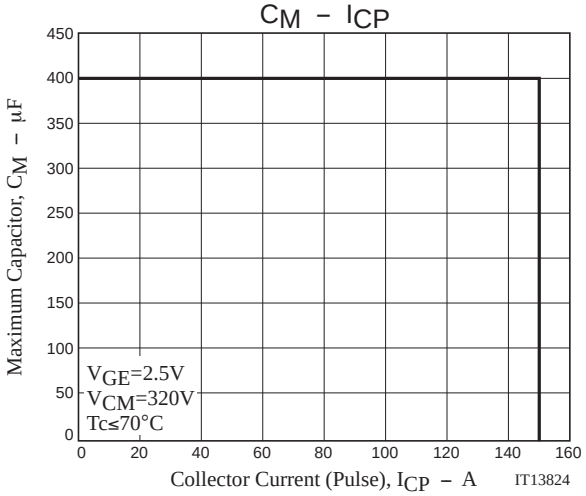
Turn OFF dv / dt – R_G



I_{CP} – V_{GE}



C_M – I_{CP}



Note : TIG052TS has protection diode between gate and emitter but handling it requires sufficient care to be taken.

This catalog provides information as of August, 2008. Specifications and information herein are subject to change without notice.